

CORRECTION

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Correction: A selectively processible instant glue passivation layer for indium gallium zinc oxide thin-film transistors fabricated at low temperature

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Correction for 'A selectively processible instant glue passivation layer for indium gallium zinc oxide thin-film transistors fabricated at low temperature' by Hyukjoon Yoo *et al.*, *J. Mater. Chem. C*, 2018, **6**, 6187–6193.

There were errors in the details shown for ref. 2, 6 and 9 cited in this article. The corrected references are shown below as ref. 1–3, respectively.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

References

- 1 J. Sheng, H.-J. Jeong, K.-L. Han, T. Hong and J.-S. Park, *J. Inf. Disp.*, 2017, **18**, 159–172.
- 2 Y. J. Tak, S. P. Park, T. S. Jung, H. Lee, W.-G. Kim, J. W. Park and H. J. Kim, *J. Inf. Disp.*, 2016, **17**, 73–78.
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